Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT186A (TO-220F) "full pack" plastic package intended for use in applications requiring high thermal cycling performance and high junction temperature capability ($T_{i(max)} = 150$ °C).

2. Features and benefits

- · High junction operating temperature capability
- High thermal cycling performance
- High voltage capability
- Planar passivated for voltage ruggedness and reliability

3. Applications

- Ignition circuits
- Motor control
- · Protection circuits e.g. SMPS inrush current
- Voltage regulation

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _h ≤ 81 °C; <u>Fig. 1</u>	-	-	10.2	А
I _{T(RMS)}	RMS on-state current	half sine wave; $T_h \le 81 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	-	16	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	-	180	A
		half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 8.3 \text{ ms}$	-	-	198	А
Tj	junction temperature		-	-	150	°C
Static characte	eristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	-	-	15	mA
Dynamic chara	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_{j} = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	A
2	Α	anode		Ġ sym037
3	G	gate		symosi
mb	n.c.	mounting base; isolated	1 2 3 TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information

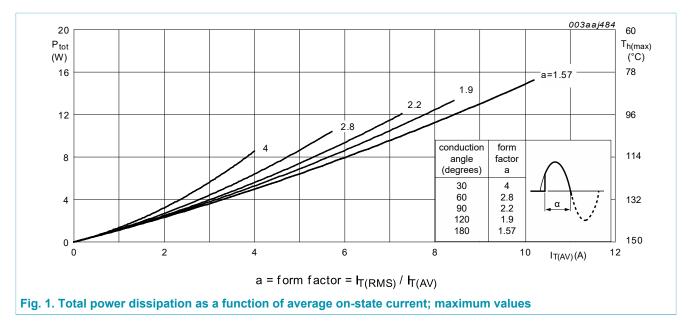
Type number	Package					
	Name	Description	Version			
TYN16X-600CT	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
V_{RRM}	repetitive peak reverse voltage		-	600	V
I _{T(AV)}	average on-state current	half sine wave; T _h ≤ 81 °C; <u>Fig. 1</u>	-	10.2	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _h ≤ 81 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	16	Α
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	180	Α
		half sine wave; T _{j(init)} = 25 °C; t _p = 8.3 ms	-	198	Α
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	162	A²s
dl _T /dt	rate of rise of on-state current	I _G = 30 mA	-	50	A/µs
I _{GM}	peak gate current		-	4	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P _{GM}	peak gate power		-	10	W
P _{G(AV)}	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C



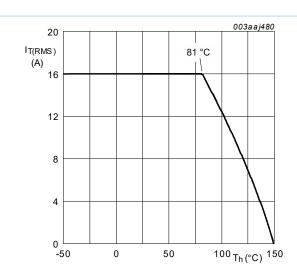


Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values

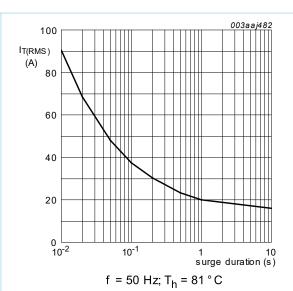


Fig. 3. RMS on-state current as a function of surge duration; maximum values

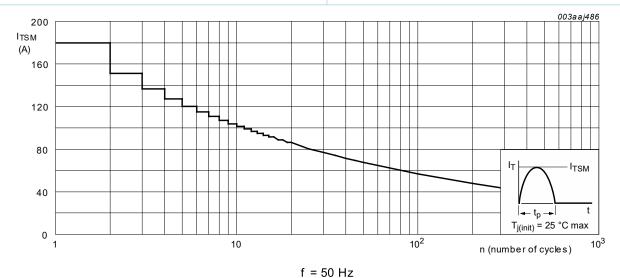
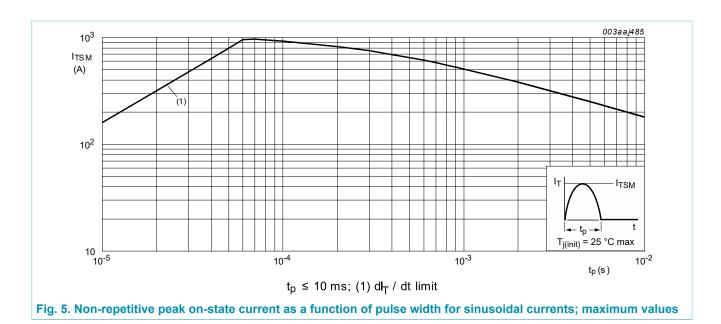


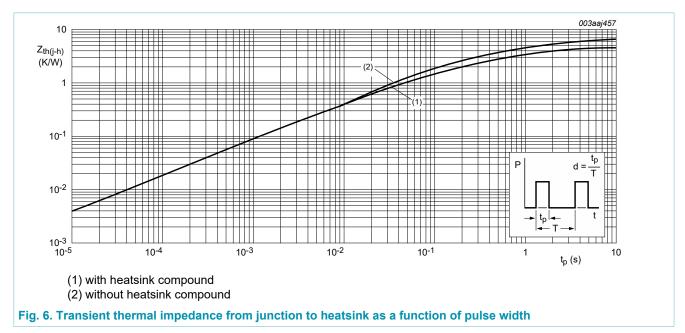
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	with heatsink compound; Fig. 6	-	-	4.5	K/W
	from junction to heatsink	without heatsink compound; Fig. 6	-	-	6.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50 \text{ Hz} \le f \le 60 \text{ Hz}$; $RH \le 65 \%$; $T_h = 25 \text{ °C}$	-	-	2500	V
C _{isol}	isolation capacitance	from anode to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

10. Characteristics

Table 7. Characteristics

Table 7. Cha	iracteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$	_	-	15	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 8$	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	40	mA
V _T	on-state voltage	I _T = 32 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
V _{GT} gat	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1.3	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C; Fig. 11	0.2	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 150 °C	-	0.2	1	mA
I _R	reverse current	V _R = 600 V; T _j = 150 °C	-	0.2	1	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	500	-	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 600 V; I_G = 100 mA; dI_G/dt = 5 A/ μ s; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 402 V; T_j = 125 °C; I_{TM} = 20 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/μs; dV_D/dt = 50 V/μs; $R_{GK(ext)}$ = 100 Ω; $(V_{DM}$ = 67% of $V_{DRM})$	-	70	-	μs

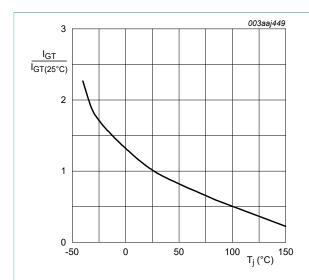


Fig. 7. Normalized gate trigger current as a function of junction temperature

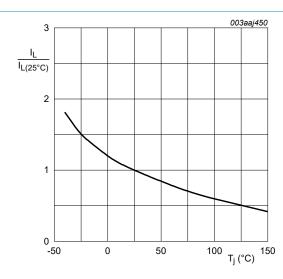


Fig. 8. Normalized latching current as a function of junction temperature

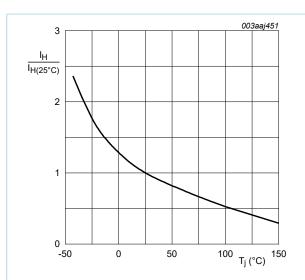
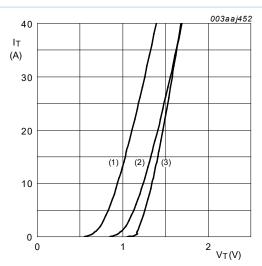


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.08 V; R_s = 0.0165 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

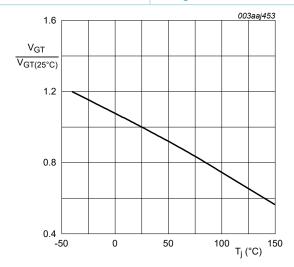


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

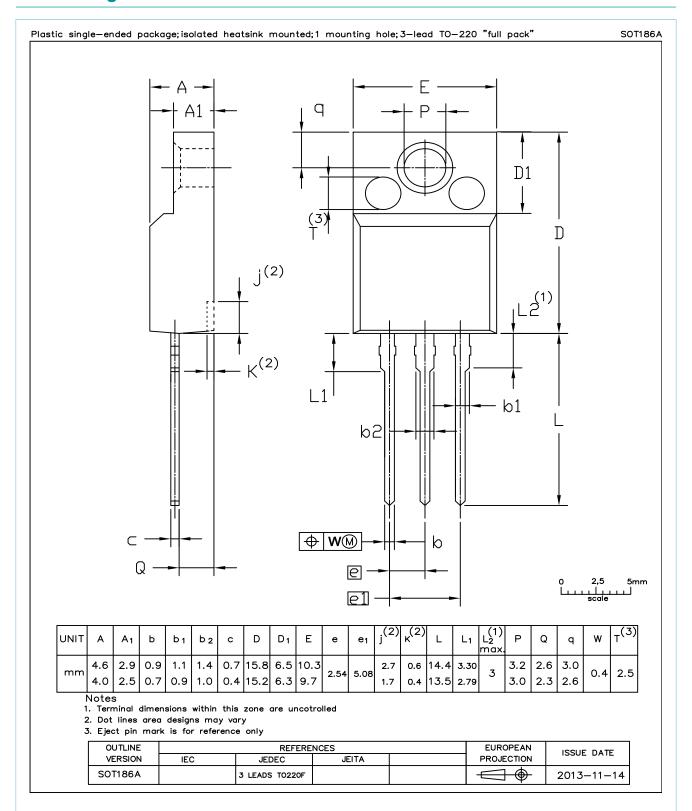


Fig. 12. Package outline TO-220F (SOT186A)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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